Doc. No.: 3026001
Issue date: March 1, 2026

Yoshiteru Nagai
General Manager

General Purose Devices Division
General Purpose Devices & Modules Headquarters
ROHM Co., Ltd.

Notification of Product/Process Change

This is an announcement of change(s) to the process of the products currently supplied by ROHM Co., Ltd.

We request your acknowledgement of the receipt of this notification within the given period.

Please provide your reply by March 31, 2027

Title of change	Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Small Signal Transistors)	
Affected product(s)	Manufacturer part number	Customer part number
	Refer attached sheet	
Detailed description of change	Before	After
	Front-end fabrication plant; Kyoto	Front-end fabrication plant; Shiga
Reason for change	As part of the consolidation of production lines, the front-end operations will be centralized at the Shiga plant.	
Anticipated impact on quality	This change will not have any impact on quality.	
Identification of change	It can be identified through traceability from the assembly lot number.	
Planned first ship date : April 1, 2027	Sample available schedule : March 1, 2026	
Comments	If you need existing products, please place your orders for the required quantities by March 31, 2027. Following the consolidated production, we would appreciate your cooperation in receiving the products in a single shipment.	

Reply date	

Customer reply	☐ 1. Approved.	☐ 2. Accepted with conditions.
Condition for approval		
Comments		
Customer company name		
Customer signature	Department	
Customer signature	Department	

Electronics for the Future

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Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Small Signal Transistors)

2026/3/1
General Purpose Devices & Modules Headquarters
General Purpose Devices Division

3026001-1. Outline of PCN

Doc. No.	3026001
Subject	Change of wafer manufacturing site from ROHM HQ Plant to Shiga Plant (Small Signal Transistors)
Background	Due to the consolidation and streamlining of manufacturing lines aimed at improving production efficiency in the Wafer process plant, the production of MOSFET currently manufactured at the Kyoto Plant will be transferred to the Shiga Plant.
Detail of change	Relocation of Front-end fabrication (Rohm HQ Plant (Kyoto)→Shiga Plant)
Affected products	Small signal transistors 6 part numbers （ Please refer to the attached documents or contact your usual ROHM contact for the actual Part Numbers affecting your company）
Required date of reply	2027/3/31
Planned date of change	2027/4/1
Last time buy date of current products	2027/3/31
Last time shipment date of current product	2028/3/31

3026001-2. Manufacturing Flow Comparison

	Current	**After Change**	
Wafer Material	8inch Epi-wafer	8inch Epi-wafer	
Wafer Process	Kyoto Plant	Shiga Plant	**Target of change**
Assembly Final Product Inspection	Assy Factory	Assy Factory	
Logistics Base	ROHM Logistics and Overseas Logistics	ROHM Logistics and Overseas Logistics	

The front-end process (wafer Process) will be transferred from the Kyoto Plant to the Shiga Plant. There are no changes to wafer materials or processes after the back-end process (package assembly process).

3026001-3. ROHM Shiga Plant Data

☐ Company name	ROHM Co.,Ltd Shiga Plant
☐ Location	2-8-1, Seiran, Otsu-City, Shiga
☐ Date established	April 20, 2015
☐ Products	MOSFET, IGBT, Diode, IPD, RASMID [*1]

＊ 1 ROHM Advanced Smart Micro Device: the ultra-small devices with ROHM’s original technology.

April. 2015	ROHM Shiga established
August. 2016	Started mass production of MOSFET
November. 2016	Started mass production of RASMIDs
August. 2017	ISO9001（2015）certified
November. 2017	ISO14001（2015）certified
December. 2017	Started mass production of diodes
August. 2018	IATF16949（2016）certification planned
August. 2018	OHSAS18001 certification planned
November. 2018	Started mass production of IGBT
April. 2020	Merged into ROHM Co., Ltd. and became ROHM Co., Ltd. Shiga Plant

3026001-4. Kyoto Plant / Shiga Plant Factory Comparison

		Current	After Change
Production Plant		Kyoto Plant	Shiga Plant
Wafer Diameter		8inch	8inch
Cleanroom	Temperature	23℃	23℃
	Humidity	45%	45%
	Cleanliness (Wafer Exposure Area)	Class3(0.1um)	Class3(0.1um)
	Airflow System	Laminar Flow	Laminar Flow
Minimum Design Rule		0.15um	0.15um

The cleanroom environment at the Shiga Plant is equivalent to that of the Kyoto Plant, and there are no issues with the production environment.

3026001-5. Summary of 4M Change Points

		Current	After Change	Comments on Change Points
Environment		Kyoto Plant	Shiga Plant	Change already implemented for other models
Man	-	Licensed operators	Licensed operators	Licensed operators at each plant
Machine	・Equipment	Existing equipment	Equivalent equipment	No issues confirmed after characteristic check
	・Process control	According to QC process chart	Managed with equivalent content	No difference
	・Management method	SPC management	Equivalent functions available	No difference
Material	・Wafer	8inch	Same material	No difference
	・Reticle size	6inch	Same design	No issues confirmed after characteristic check
	・Others	Chemicals, wiring materials, etc.	Equivalent performance materials	No issues confirmed after characteristic check
Method	・Work method	Work standards	Equivalent standards	No differences in work procedures
	・Inspection	According to inspection standards	Equivalent content	No difference
	・Traceability	15 years	Managed with equivalent content	No difference
Measurement	・Measuring equipment	Existing equipment	Equivalent type of equipment	Equipment correlation completed, no issues
	・Management method	According to equipment QC process chart	Equivalent management content	No difference

We have confirmed that there are no issues with any of the items in accordance with the 4M change points.

3026001-6. Extraction of Concerns and Confirmation Results

Item	Concern	Before Change (HQ)	After Change (Shiga)	Judgment
Electrical Characteristics	Variation in characteristics	Standard	Equivalent to HQ product	No problem
Yield	Yield decrease	Standard	No decrease compared to HQ product	No problem
Primary Characteristics	Variation in primary characteristics	Standard	Equivalent to HQ product (Refer to the following)	No problem

<Primary Characteristics_Process Capability Index Comparison Results> 0.15µm MOSFET Product Quality

No.	Process	Before Change (HQ)	After Change (Shiga)	Judgment
		Cpk	Cpk	
1	Trench Dimension	1.35	1.64	No Issue
2	Trench Depth	1.41	1.43	No Issue
3	Gate Oxide Thickness	2.11	2.51	No Issue
4	Gate Poly-Si Thickness	3.31	4.43	No Issue
5	ILD Thickness	2.45	2.87	No Issue
6	Contact Dimension	1.98	2.16	No Issue
7	Cont Depth	1.35	1.39	No Issue

All concerns have been confirmed to present no issues.

3026001-7. Reliability test result

1. Test result

Test item	Test conditions	Standard	Test time	n(pcs)	Failure Pn (pcs)
Temperature humidity bias (THB)	Ta=85℃, Rh=85%, Vds-max	JESD22-A101	1,000h	22pcs	0
Temperature cycle (TCY)	-55℃ (30min) - +150℃ (30min)	JESD22-A104	200cyc	22pcs	0
Pressure cooker (PCT)	Ta=121℃, 15psig, Rh=100%	JESD22-A102	100h	22pcs	0
High temperature reverse bias (HTRB)	Ta=150℃, Vds-max	JESD22-A108	1,000h	22pcs	0
High temperature gate bias (HTGB)	Ta=150℃, Vgs-max	JESD22-A108	1,000h	22pcs	0

2. Measurement Item & Criteria

Item	Condition	Criteria
		Electrical characteristic
BVDSS, VGS	Par specification	Must be in the values specified in specification sheet.
IGSS, IDSS,IDGO	Par specification	
Vgs(th), Rds(on), Yfs	Par specification	
Appearance	Visual inspection	No significant change

Reliability test results show no problem.

ROHM
SEMICONDUCTOR

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ROHM Co.,Ltd.

Public（External) PN
RV5A040APTCR1
RV5C040APTCR1
RV2C014BCT2CL
RV2E012ATT2CL
RV2E014AJT2CL
RV7L020GNTCR1